

www.vishay.com

VS-ST330CL

Vishay Semiconductors

Phase Control Thyristors (Hockey PUK Version), 650 A



B-PUK (TO-200AC)

PRIMARY CHARACTERISTICS IT(AV) 650 A VDRM/VRRM 400 V, 800 V, 1200 V, 1400 V, 1600 V VTM 1.90 V IGT 100 mA TJ -40 °C to +125 °C Package B-PUK (TO-200AC) Circuit configuration Single SCR

FEATURES

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case B-PUK (TO-200AC))
- High profile hockey PUK
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	TEST CONDITIONS	VALUES	UNITS				
1		650	A				
I _{T(AV)}	T _{hs}	55	°C				
1		1230	A				
I _{T(RMS)}	T _{hs}	25	°C				
1	50 Hz	9000	0				
I _{TSM}	60 Hz	9420	- A				
l ² t	50 Hz	405	– kA ² s				
1-1	60 Hz	370	KA-S				
V _{DRM} /V _{RRM}		400 to 1600	V				
t _q	Typical	100	μs				
TJ		-40 to +125	°C				

ELECTRICAL SPECIFICATIONS

VOLTAGE F	VOLTAGE RATINGS										
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I _{DRM} /I _{RRM} MAXIMUM AT T _J = T _J MAXIMUM mA							
	04	400	500								
	08	800	900								
VS-ST330CL	12	1200	1300	50							
	14	1400	1500								
	16	1600	1700								

Revision: 09-Jan-2025 1 Document Number: 94408 For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



COMPLIANT



www.vishay.com

VS-ST330CL

Vishay Semiconductors

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL		TEST CON	IDITIONS	VALUES	UNITS	
Maximum average on-state current		180° condu	ction, half sine	wave	650 (314)	А	
at heatsink temperature	I _{T(AV)}	double side	(single side) co	oled	55 (75)	°C	
Maximum RMS on-state current	I _{T(RMS)}	DC at 25 °C	heatsink temp	erature double side cooled	1230		
		t = 10 ms	No voltage		9000		
Maximum peak, one-cycle		t = 8.3 ms	reapplied		9420	А	
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		7570		
		t = 8.3 ms	reapplied	Sinusoidal half wave,	7920		
		t = 10 ms	No voltage	initial $T_J = T_J$ maximum	405	- kA ² s	
Maximum I ² t for fusing	l ² t	t = 8.3 ms	reapplied		370		
	1-1	t = 10 ms	100 % V _{RRM}		287		
		t = 8.3 ms	reapplied		262		
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 to 10) ms, no voltage	reapplied	4050	kA²√s	
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.91	v	
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J maximum$				
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum			0.57	mΩ	
High level value of on-state slope resistance	r _{t2}	$(l > \pi \times I_{T(AV)}), T_J = T_J maximum$			0.57	11152	
Maximum on-state voltage	V_{TM}	$I_{pk} = 1730 \text{ A}, T_J = T_J \text{ maximum, } t_p = 10 \text{ ms sine pulse}$			1.90	V	
Maximum holding current	Ι _Η	T - 25 °C	anada ayanby 1	2. V registive lead	600	mA	
Typical latching current	١L	$i_{\rm J} = 25^{-1}$ C,	anoue supply 1	2 V resistive load	1000	IIIA	

SWITCHING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega, t_r \leq 1 \; \mu s$ $T_J = T_J$ maximum, anode voltage $\leq 80 \; \% \; V_{DRM}$	1000	A/µs				
Typical delay time t _d		Gate current 1 A, dl _g /dt = 1 A/ μ s V _d = 0.67 % V _{DRM} , T _J = 25 °C	1.0	110				
Typical turn-off time	tq	I_{TM} = 550 A, T_J = T_J maximum, dl/dt = 40 A/µs, V_R = 50 V, dV/dt = 20 V/µs, gate 0 V 100 $\Omega,$ t_p = 500 µs	100	μs				

BLOCKING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/µs			
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	50	mA			



www.vishay.com

VS-ST330CL

Vishay Semiconductors

TRIGGERING						
PABAMETER	SYMBOL	TEST CONDITIONS			VALUES	
FARAMETER	STIVIDOL	TEX	ST CONDITIONS	Тур.	Max.	UNITS
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum,	t _p ≤ 5 ms	10	0.0	w
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	vv
Maximum peak positive gate current	I _{GM}	$T_J = T_J$ maximum,	t _p ≤ 5 ms	3	.0	А
Maximum peak positive gate voltage	$+V_{GM}$		t < 5 mc	2	20	v
Maximum peak negative gate voltage	-V _{GM}	$T_J = T_J$ maximum, $t_p \le 5$ ms			.0	v
	I _{GT}	T _J = -40 °C			-	
DC gate current required to trigger		T _J = 25 °C		100	200	mA
		T _J = 125 °C	Maximum required gate trigger/ current/voltage are the lowest	50	-	
		T _J = -40 °C	value which will trigger all units 12 V anode to cathode applied	2.5	-	
DC gate voltage required to trigger	V _{GT}	T _J = 25 °C			3.0	V
		T _J = 125 °C			-	
DC gate current not to trigger	I _{GD}	T T movimum	Maximum gate current/voltage not to trigger is the maximum	1	0	mA
DC gate voltage not to trigger	V _{GD}	$T_J = T_J$ maximum	value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.25		v

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating junction temperature range	TJ		-40 to +125	℃		
Maximum storage temperature range	T _{Stg}		-40 to +150			
Movimum thermal registence, junction to heataink	Р	DC operation single side cooled	0.11			
Maximum thermal resistance, junction to heatsink	R _{thJ-hs}	DC operation double side cooled	0.06	K/W		
Maximum thermal registeres, ease to be tainly	Р	DC operation single side cooled	0.011	r∨ vv		
Maximum thermal resistance, case to heatsink	R _{thC-hs}	DC operation double side cooled	0.005			
Mounting force, ± 10 %			9800 (1000)	N (kg)		
Approximate weight			250	g		
Case style		See dimensions - link at the end of datasheet	B-PUK (TO-	200AC)		

CONDUCTION ANGLE	SINUSOIDAL CONDUCTION RECTANGULAR CONDUCTION				TEST CONDITIONS	UNITS		
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TESTCONDITIONS	UNITS		
180°	0.012	0.010	0.008	0.008				
120°	0.014	0.015	0.014	0.014				
90°	0.018	0.018	0.019	0.019	$T_J = T_J$ maximum	K/W		
60°	0.026	0.027	0.027	0.028				
30°	0.045	0.046	0.046	0.046				

Note

• The table above shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC

Revision: 09-Jan-2025 3 Document Number: 94408 For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



www.vishay.com

VS-ST330CL

Vishay Semiconductors

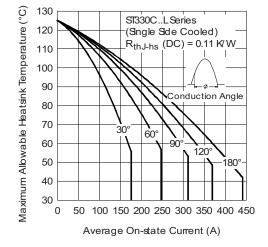


Fig. 1 - Current Ratings Characteristics

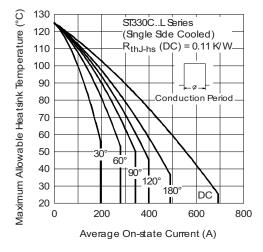


Fig. 2 - Current Ratings Characteristics

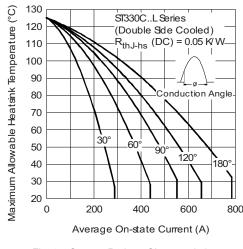


Fig. 3 - Current Ratings Characteristics

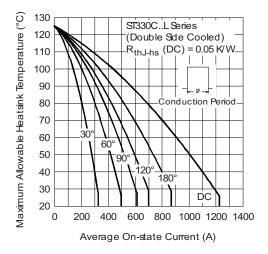


Fig. 4 - Current Ratings Characteristics

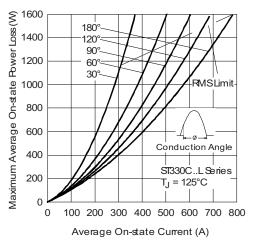
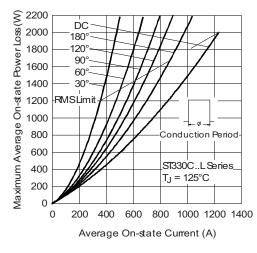
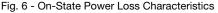


Fig. 5 - On-State Power Loss Characteristics





Revision: 09-Jan-2025

4

Document Number: 94408

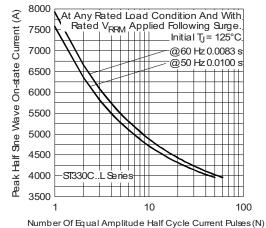
For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



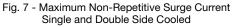
www.vishay.com

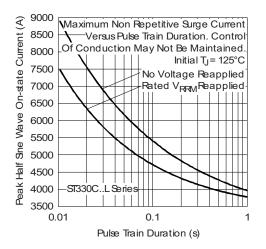
Vishay Semiconductors

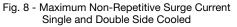
VS-ST330CL

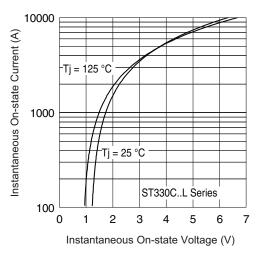


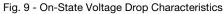


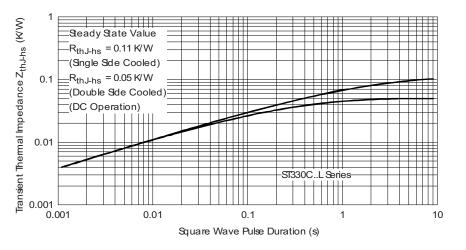


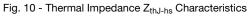












Revision: 09-Jan-2025	5	Document Number: 94408
For technical questions within your region:	: DiodesAmericas@vishay.com, DiodesAsia@vish	ay.com, DiodesEurope@vishay.com
	E WITHOUT NOTICE. THE PRODUCTS DESCRII CIFIC DISCLAIMERS, SET FORTH AT <u>www.visha</u> y	



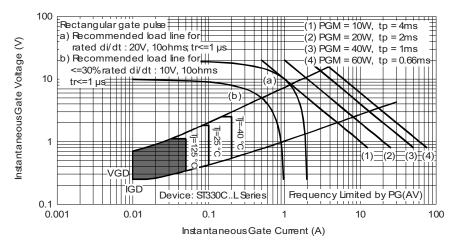


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	ST	33	0	С	16	L	1	-	
	1	2	3	4	5	6	7	8	9	
	1 -	Visl	nay Sen	niconduo	ctors pro	oduct				
	2 -	Thy	ristor							
	3 -	Ess	ential p	art numl	ber					
	4 -	0 =	convert	er grade	9					
	5 -	C =	cerami	DUK						
	6 -	Vol	Voltage code x 100 = V _{RRM} (see Voltage Ratings table)							
	7 -	L =	L = PUK case B-PUK (TO-200AC)							
	8 -	0 =	0 = eyelet terminals (gate and auxiliary cathode unsoldered leads)							
		1 =	1 = fast-on terminals (gate and auxiliary cathode unsoldered leads)							
		2 =	eyelet t	erminals	s (gate a	nd auxi	liary ca	thode s	oldered leads)	
		3 =	fast-on t	erminals	(gate ar	nd auxilia	ary cath	ode sold	lered leads)	
	9 -		ical dV/		-		-			
					= 1000 V	-	-			

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95076				

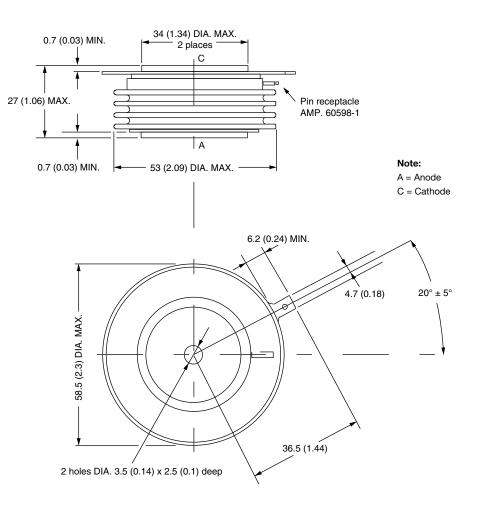
Vishay Semiconductors



B-PUK (TO-200AC)

DIMENSIONS in millimeters (inches)

Creepage distance: 36.33 (1.430) minimum Strike distance: 17.43 (0.686) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Vishay products are not designed for use in life-saving or life-sustaining applications or any application in which the failure of the Vishay product could result in personal injury or death unless specifically qualified in writing by Vishay. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

© 2025 VISHAY INTERTECHNOLOGY, INC. ALL RIGHTS RESERVED

Revision: 01-Jan-2025

1